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- **Member of the Texas Instruments** Widebus™ Family
- **EPIC** ™ (Enhanced-Performance Implanted **CMOS) Submicron Process**
- Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- **ESD Protection Exceeds 2000 V Per** MIL-STD-883. Method 3015: Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per **JESD 17**
- Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages

description

This 16-bit registered transceiver is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74ALVCH16543 can be used as two 8-bit transceivers or one 16-bit transceiver. Separate latch-enable (LEAB or LEBA) and output-enable (OEAB or OEBA) inputs are provided for each register to permit independent control in either direction of data flow.

The A-to-B enable (CEAB) input must be low to enter data from A or to output data from B. If CEAB is low and LEAB is low, the A-to-B latches are transparent; a subsequent low-to-high transition of LEAB puts the A latches in the storage mode. With CEAB and OEAB both low, the 3-state B outputs are active and reflect the data present at the output of the A latches. Data flow from B to A is similar, but requires using CEBA, LEBA, and OEBA.

DGG OR DL PACKAGE (TOP VIEW)

1OEAB	1	\cup	56	1 <mark>OEBA</mark>
1LEAB	2		55	1LEBA
1CEAB	3		54	1CEBA
GND [4		53] GND
1A1 [5		52] 1B1
1A2 [6		51] 1B2
v _{cc} [7		50] v _{cc}
1A3 [8		49] 1B3
1A4	9		48] 1B4
1A5 [10		47	
GND	11		46] GND
1A6			45] 1B6
1A7	13		44] 1B7
1A8	1 ' '		43] 1B8
2A1 [15		42] 2B1
2A2	1		41] 2B2
2A3 [17		40] 2B3
GND [18		39	
2A4 [1		38] 2B4
2A5 [20		37] 2B5
2A6 [21		36] 2B6
V _{CC} [22		35] v _{cc}
2A7 [23		34] 2B7
2A8 [24		33] 2B8
GND [25		32] GND
2CEAB	26		31	2CEBA
2LEAB	27		30	2LEBA
2 <mark>0EAB</mark> [28		29	2OEBA
				•

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

The SN74ALVCH16543 is characterized for operation from -40°C to 85°C.



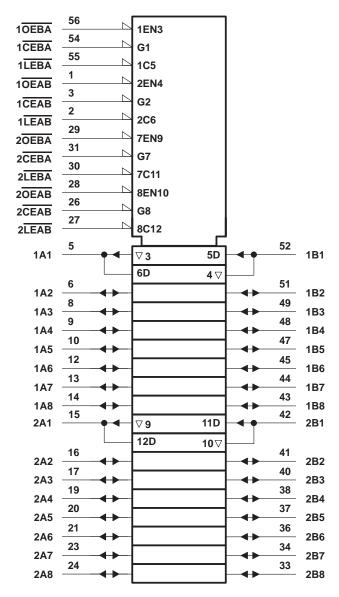
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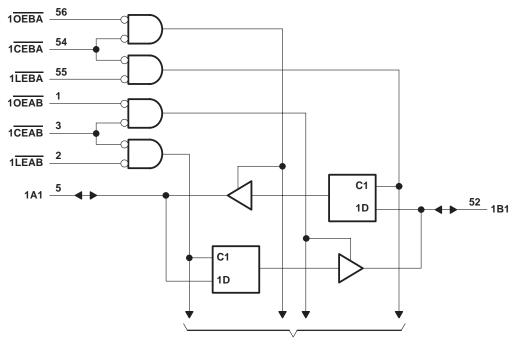
logic symbol†



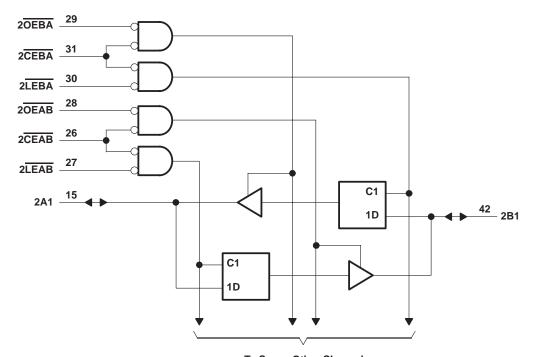
[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



logic diagram (positive logic)



To Seven Other Channels



To Seven Other Channels

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FUNCTION TABLE† (each 8-bit section)

	INPUTS					
CEAB	LEAB	OEAB	Α	В		
Н	Х	Х	Χ	Z		
Х	Χ	Н	Χ	Z		
L	Н	L	Χ	в ₀ ‡		
L	L	L	L	L		
L	L	L	Н	Н		

[†] A-to-B data flow is shown; B-to-A flow control is the same except that it uses CEBA, LEBA, and OEBA.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)§

Supply voltage range, V _{CC}	0.5 V to 4.6 V
Input voltage range, V _I : Except I/O ports (see Note 1)	
I/O ports (see Notes 1 and 2)	
Output voltage range, VO (see Notes 1 and 2)	0.5 V to V _{CC} + 0.5 V
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Continuous output current, IO	±50 mA
Continuous current through each V _{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package	81°C/W
DL package	74°C/W
Storage temperature range, T _{stq}	65°C to 150°C

[§] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. This value is limited to 4.6 V maximum.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.



[‡] Output level before the indicated steady-state input conditions were established

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recommended operating conditions (see Note 4)

			MIN	MAX	UNIT	
Vcc	Supply voltage		1.65	3.6	V	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	0.65 × V _{CC}			
٧ıH	High-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2			
VIL		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		$0.35 \times V_{CC}$		
	Low-level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
		$V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8		
٧ _I	Input voltage		0	VCC	V	
٧o	Output voltage		0	VCC	V	
		V _{CC} = 1.65 V		-4		
la	High-level output current	V _{CC} = 2.3 V		-12	mA	
ЮН		V _{CC} = 2.7 V		-12] ""A	
		V _{CC} = 3 V		-24		
		V _{CC} = 1.65 V		4		
la.	Law layed autout average	V _{CC} = 2.3 V		12		
lOL	Low-level output current	V _{CC} = 2.7 V		12	mA	
		V _{CC} = 3 V		24		
Δt/Δν	Input transition rise or fall rate			10	ns/V	
T _A	Operating free-air temperature		-40	85	°C	

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAF	RAMETER	TEST C	ONDITIONS	v _{cc}	MIN	TYP [†]	MAX	UNIT	
		I _{OH} = -100 μA		1.65 V to 3.6 V	V _{CC} -0	.2			
		I _{OH} = -4 mA		1.65 V	1.2				
		I _{OH} = -6 mA		2.3 V	2				
Vон				2.3 V	1.7			V	
		I _{OH} = -12 mA		2.7 V	2.2				
				3 V	2.4				
		I _{OH} = -24 mA		3 V	2				
		I _{OL} = 100 μA		1.65 V to 3.6 V			0.2		
		$I_{OL} = 4 \text{ mA}$	I _{OL} = 4 mA				0.45		
VoL	$I_{OL} = 6 \text{ mA}$	2.3 V			0.4	V			
	I _{OL} = 12 mA	2.3 V			0.7	V			
		IOL = 12 IIIA	2.7 V				0.4		
		I _{OL} = 24 mA	3 V				0.55		
Ц		$V_I = V_{CC}$ or GND		3.6 V			±5	μА	
		V _I = 0.58 V	1.65 V	25					
		V _I = 1.07 V	1.65 V	-25					
		V _I = 0.7 V		2.3 V	45				
II(hold)		V _I = 1.7 V	2.3 V	-45			μΑ		
		V _I = 0.8 V	3 V	75					
		V _I = 2 V	3 V	-75					
		$V_{I} = 0 \text{ to } 3.6 \text{ V}^{\ddagger}$		3.6 V			±500		
l _{OZ} §		$V_O = V_{CC}$ or GND		3.6 V			±10	μΑ	
Icc		$V_I = V_{CC}$ or GND,	IO = 0	3.6 V			40) μΑ	
ΔlCC		One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND		3 V to 3.6 V			750	μΑ	
Ci	Control inputs	$V_I = V_{CC}$ or GND		3.3 V		3.5		pF	
C _{io}	A or B ports	$V_O = V_{CC}$ or GND		3.3 V		8.5		pF	

[†] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

			V _{CC} =	1.8 V	V _{CC} =	2.5 V 2 V	VCC =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _W	t _W Pulse duration, LE or CE low		¶		3.3		3.3		3.3		ns
t _{su}	Setup time	Data before LE↑ or CE↑	¶		1.2		1.5		1.2		ns
t _h	Hold time	Data after LE↑ or CE↑	¶		1.2		0.8		1.3		ns

This information was not available at the time of publication.



[‡] This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

 $[\]mbox{\ensuremath{\,\mathbb{S}}}$ For I/O ports, the parameter IOZ includes the input leakage current.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V	V _{CC} =	2.5 V 2 V	VCC =	2.7 V	V _{CC} =	3.3 V 3 V	UNIT
	(INFOT)	(001701)	TYP	MIN	MAX	MIN	MAX	MIN	MAX	
	A or B	B or A	†	1	5.1		4.8	1	4.3	no
^t pd	LE	A or B	†	1	6.5		6.2	1.1	5	ns
t _{en}	CE	A or B	†	1	7.2		6.9	1	5.6	ns
t _{dis}	CE	A or B	†	1.3	6.1		6.2	1.5	5.1	ns
t _{en}	ŌĒ	A or B	†	1	6.8		6.3	1	5.3	ns
t _{dis}	ŌĒ	A or B	†	1	5.7		4.8	1.1	4.6	ns

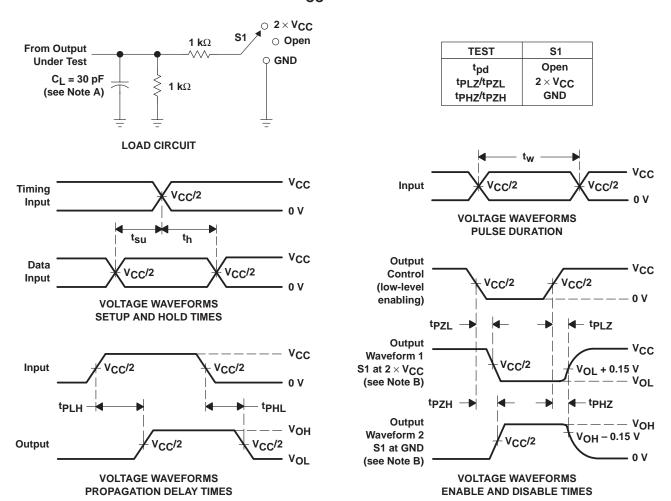
[†] This information was not available at the time of publication.

operating characteristics, $T_A = 25^{\circ}C$

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	UNIT	
	PARAMETER		TEST CONDITIONS	TYP	TYP	TYP	UNII
	Power dissipation	Outputs enabled	C ₁ = 50 pF. f = 10 MHz	†	54	64	pF
C _{pd}	capacitance	Outputs disabled	$C_L = 50 \text{ pF}, f = 10 \text{ MHz}$	†	6	7	рг

[†] This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V}$



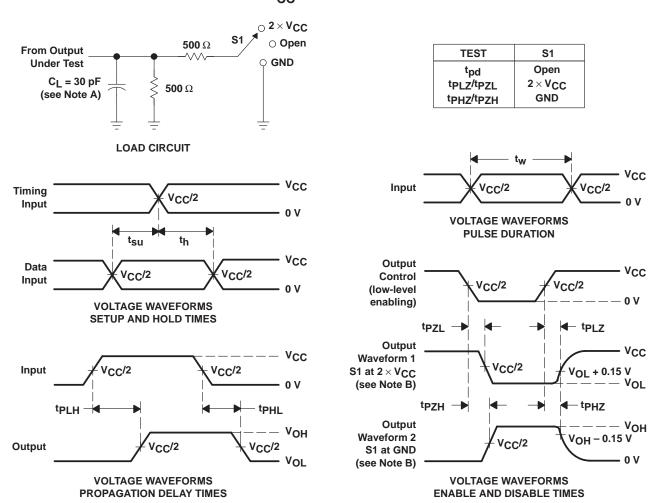
- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLZ and tpHZ are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



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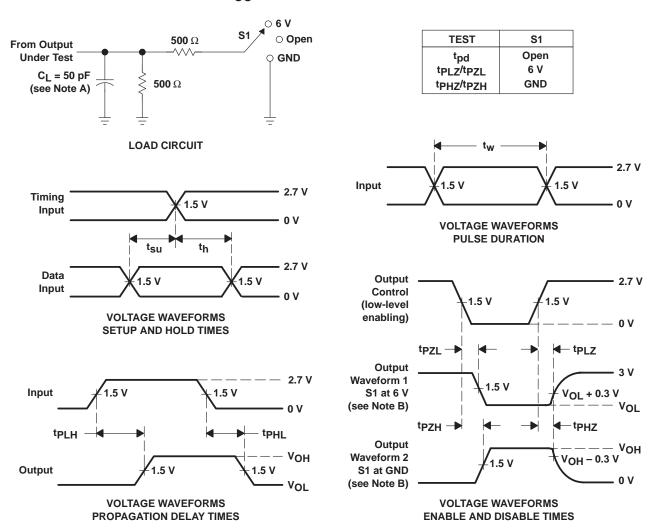
PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.5 V \pm 0.2 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{O} = 50 $\Omega,\,t_{f}\leq$ 2 ns, $t_{f}\leq$ 2 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpLZ and tpHZ are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tplH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION V_{CC} = 2.7 V AND 3.3 V \pm 0.3 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , $t_r \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. tpl 7 and tpH7 are the same as tdis.
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

Figure 3. Load Circuit and Voltage Waveforms



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